

High Power Current sensors

Metal Foil Current Sensing Resistors

Features

- ◆ Chip size 1225: Resistance value from 0.25mΩ up to 10mΩ
- ◆ Chip size 2512: Resistance value from 1mΩ up to 1000mΩ
- ◆ Lead free, RoHs compliant for global applications and halogen free
- ◆ Excellent long term stability

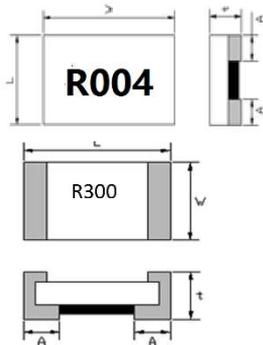
Application

- ◆ Switching Power Supply
- ◆ Voltage Regulation Module
- ◆ DC-DC Converter, Adaptor, Battery Pack, Charger
- ◆ PDA & Cell Phone
- ◆ Power management Applications
- ◆ Current sensor for power hybrid sources
- ◆ High current handling for automotive engine

1. High Power Metal Foil-Current Sensing Resistors

This approval sheet applies of high-power metal foil current sensing resistor

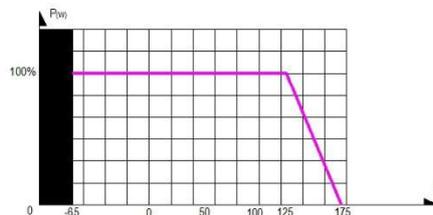
2. Dimensions



Type (inch size)	Dimensions(mm)			
	L	W	t	A
LFS1225	3.1±0.15	6.3±0.15	0.80±0.15	0.55±0.15

Type (inch size)	Dimensions(mm)			
	L	W	t	A
LFS 2512	6.45±0.20	3.25±0.20	0.80±0.15	0.90±0.20

3. Derating Curve



4. Ordering code

LFS 1225 E F H R004
 (1) (2) (3) (4) (5) (6)

(1) Series type: LFS (High Power Metal Foil Current Sensing Resistor)

(2) Chip size: 1225; 2512

(3) Packaging Material: Emboss (E)

(4) Resistance Tolerance: ± 1% (F), ± 2% (G), ± 5% (J)

(5) Power rating: H=3W

(6) Resistance Code: R004 means 4mΩ,

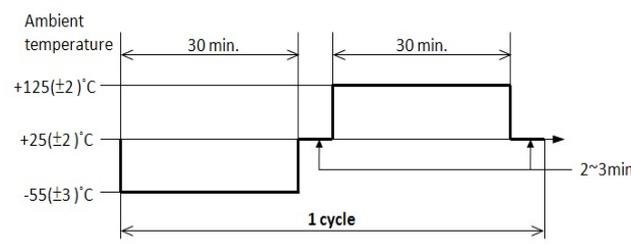
5. Electrical Specification

Item	Power Rating	Resistance Range(mΩ)	Tolerance (%)	TCR (PPM/°C)
LFS 1225	3W	0.25 ≤ R ≤ 10	F(±1.0); J(±5.0); K(±10)	±50;
LFS 2512	3W	1 ≤ R ≤ 1000	F(±1.0); J(±5.0); K(±10)	±50;

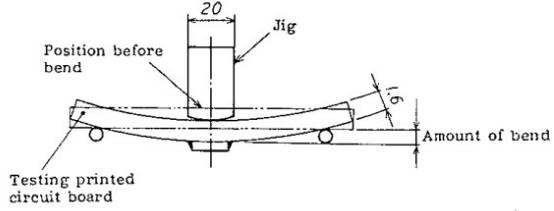
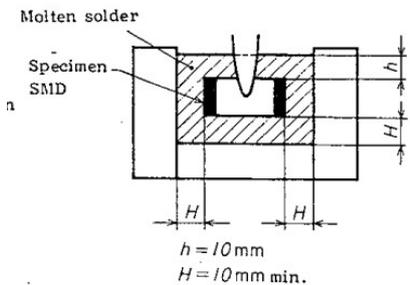
Unless otherwise specified, all values are tested at the following condition:

Temperature: 21°C to 25°C and Relative humidity: 45% to 75%

6. Environmental Characteristics

No.	Item	Test Condition	Specification
1	Temperature Coefficient of Resistance (T.C.R.)	+25°C /+125°C. (JIS-C5202-5.2) $TCR \text{ (ppm/}^\circ\text{C)} = \frac{\Delta R}{R \times \Delta t} \times 10^6$	Refer to electrical specification.
2	Damp Heat with Load	The specimens shall be placed in a chamber and subjected to a relative humidity of 90~95% percent and a temperature of 40° ±2°C for the period of 1000 hr with applying rated power 1.5 hours ON and 0.5 hour OFF. (MIL-STD-202, Method 103)	$\Delta R \leq \pm(1\% + 0.0005\Omega)$
3	High Temperature Exposure	The chip (mounted on board) is exposed in the heat chamber 125±3°C for 1000 hrs. (JIS-C5202-7.2)	$\Delta R \leq \pm(1\% + 0.0005\Omega)$
4	Load Life	Apply rated power at 70±2°C for 1000 hours with 1.5 hours ON and 0.5 hour OFF. (JIS-C5202-7.10)	$\Delta R \leq \pm(1\% + 0.0005\Omega)$
5	Rapid change of temperature	The chip (mounted on board) is exposed, -55±3°C (30min.)/+155±2°C (30min.) for 5 cycles. The following conditions as the following figure. (JIS-C5202-7.4) 	$\Delta R \leq \pm(1\% + 0.0005\Omega)$

7. Function Performance

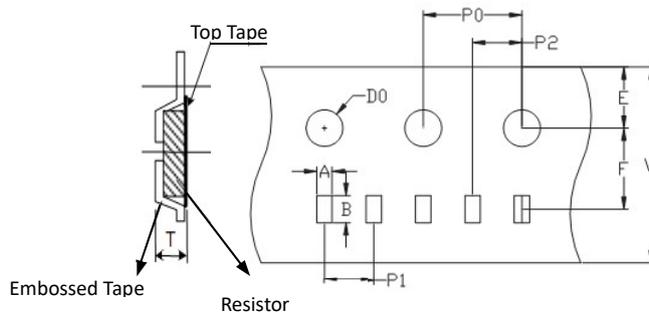
No.	Item	Test Condition	Specification
1	Bending Strength	<p>Mount the chip to test substrate. Apply pressure in direction of arrow unit band width reaches 2mm(+0.2/-0mm) illustrated in the figure below and hold for 10±1 sec. (JIS-C5202-6.1)</p> <p style="text-align: right;">Unit: mm</p> 	$\Delta R \leq \pm(1\% + 0.0005\Omega)$
2	Solvent Resistance	<p>The chip is completed immersion of the specimens in the isopropyl alcohol for 3 (+5, -0) min. at 25°C ±5°C. (MIL-STD-202, Method 215)</p>	Verify marking permanency. (Nor required for laser etched parts or parts with no marking)
3	Resistance to solder Heat	<p>The specimen chip shall be immersed into the flux specified in the solder bath 260±5°C for 10±1 sec. (MIL-STD-202, Method 210)</p>	$\Delta R \leq \pm(1\% + 0.0005\Omega)$
4	Solderability	<p>The specimen chip shall be immersed into the flux specified in the solder bath 235±5°C for 2±0.5 sec. It shall be immersed to a point 10mm from its root. (Sn96.5/Ag3.0/Cu0.5) (JIS-C5 202-6.11)</p> 	Solder shall be covered 95% or more of the electrode area.

Remark:

a. 3.0 W with total solder pad trace size of 300 mm². The surface temperature of component should below 100°C.

8. Tape Packaging Specifications

◆ Embossed Plastic Tape Specifications



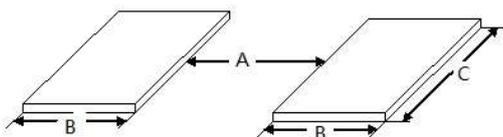
Type	Carrier Dimensions (mm)									
	A	B	E	F	W	P0	P1	P2	D0	T
1225	3.5±0.1	6.8±0.1	1.75±0.1	5.5±0.05	12.0±0.2	4.0±0.05	4.0±0.1	2.0±0.05	1.5±0.1	1.0±0.2
Type	Carrier Dimensions (mm)									
	A	B	E	F	W	P0	P1	P2	D0	T
2512	3.5±0.1	6.8±0.1	1.75±0.1	5.5±0.05	12.0±0.2	4.0±0.05	4.0±0.1	2.0±0.05	1.5±0.1	1.0±0.2

9. Minimum packaging quantity

Size EIA (EIAJ)	1225,2512
Standard Packing Quantity (pcs /reel)	4,000

10. Storage Conditions

Temperature : 5~35°C, Humidity : 40~75%



11. Recommended Soldering Pad Layout

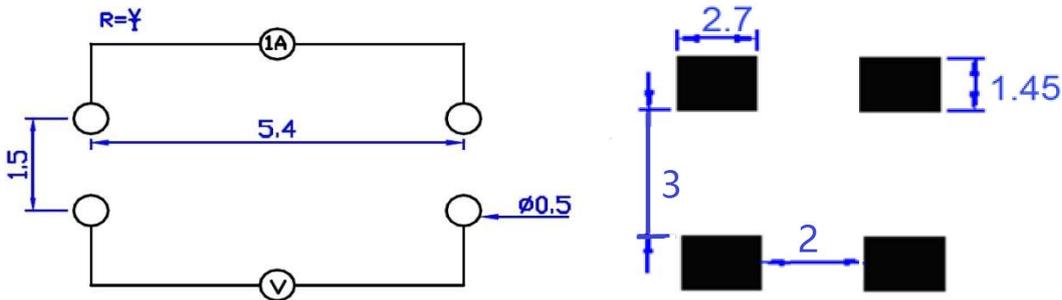
Type	Pad Layout Dimension (mm)		
	A	B	C
1225	1.20	2.00	7.00
2512	3.80	2.10	3.40

12. Measurements:

12.1 Excitation current should be 3A for resistance lower than 5mΩ

12.2 Excitation current should be 1A for resistance higher than 5mΩ

12.3 4-wire precision measurement layout and 4 wire pads layout



13. Soldering Recommendations

- ◆ Peak reflow temperatures and durations :
 - IR Reflow Peak = 260°C max for 10 sec
 - Wave Solder = 260°C max for 10 sec
- ◆ Compatible with lead and lead-free solder reflow processes
- ◆ Recommended IR Reflow Profile :

